

3D silicon sensors at FBK: first results on the last production

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The talk will present the last batch of 3D n-on-p detectors produced by FBK-CMM designed for LHC Phase-2 Upgrade. The process was performed both on Si-Si and SOI wafers with 130 μm device thickness. Several kinds of pixel detectors, e.g., compatible with read-out chips such as FE-I4, CMS and RD53A, have been realized on wafers. We will report on the sensor technology and offer an overview of the first electrical characterization of the devices we have produced. This activity was supported by AIDA 2020 and INFN (ATLAS - CMS) - FBK Pixel R&D Collaboration.

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